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AMENDMENT TRANSMITTAL LETTER			Docket No. M4065.0900/P900		
Application No. 10/822,785-Conf. #3196	Filing Date April 13, 2004	Examiner E. J. Wendler	Art Unit 2824		
Applicant(s): Ramin Ghodsi					
Invention: MULTI-CELL RESISTIVE MEMORY ARRAY ARCHITECTURE WITH SELECT TRANSISTOR					
TO THE COMMISSIONER FOR PATENTS					
Transmitted herewith is an Amendment Under 37 CFR 1.312 in the above-identified application. The fee has been calculated as shown below.					
CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	22	- 22 =	0	x	0
Independent Claims	9	- 9 =	0	x	0
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					0
Other fee (please specify):					0
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity					
<input checked="" type="checkbox"/> No additional fee is required for this Amendment.					
<input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of \$ _____.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Director is hereby authorized to charge and credit Deposit Account No. <u>04-1073</u> as described below.					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 Thomas J. D'Amico Attorney/Agent Reg. No.: 28,371 DICKSTEIN SHAPIRO LLP 1825 Eye Street, NW Washington, DC 20006-5403 (202) 420-2232			Dated: <u>September 28, 2006</u>		



Docket No.: M4065.0900/P900
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ramin Ghodsi

Allowed: July 14, 2006

Application No.: 10/822,785

Confirmation No.: 3196

Filed: April 13, 2004

Art Unit: 2824

For: MULTI-CELL RESISTIVE MEMORY
ARRAY ARCHITECTURE WITH SELECT
TRANSISTOR

Examiner: E. J. Wendler

AMENDMENT UNDER 37 C.F.R. § 1.312

MS Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

Prior to issuance, please amend the above-captioned application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 10 of this paper.